

# Joanna L Batstone

## List of Publications by Year in descending order

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69  
papers

1,628  
citations

361413

20  
h-index

289244

40  
g-index

69  
all docs

69  
docs citations

69  
times ranked

591  
citing authors

#	ARTICLE	IF	CITATIONS
1	Silicide formation and silicide-mediated crystallization of nickel-implanted amorphous silicon thin films. Journal of Applied Physics, 1993, 73, 8279-8289.	2.5	350
2	In situ transmission electron microscopy studies of silicide-mediated crystallization of amorphous silicon. Applied Physics Letters, 1992, 60, 225-227.	3.3	117
3	Luminescence studies of individual dislocations in II-VI (ZnSe) and III-V (InP) semiconductors. Journal of Physics C: Solid State Physics, 1984, 17, 6477-6492.	1.5	94
4	Evidence for the influence of interfacial atomic structure on electrical properties at the epitaxial CoSi <sub>2</sub> /Si(111) interface. Physical Review Letters, 1988, 60, 1394-1397.	7.8	84
5	In situ study of the molecular beam epitaxy of CoSi <sub>2</sub> on (111)-Si by transmission electron microscopy and diffraction. Applied Physics Letters, 1987, 51, 45-47.	3.3	81
6	Mechanisms of buried oxide formation by ion implantation. Applied Physics Letters, 1987, 50, 19-21.	3.3	77
7	Control of pinholes in epitaxial CoSi <sub>2</sub> layers on Si(111). Applied Physics Letters, 1988, 52, 648-650.	3.3	72
8	In situ crystallization of amorphous silicon in the transmission electron microscope. Philosophical Magazine A: Physics of Condensed Matter, Structure, Defects and Mechanical Properties, 1993, 67, 51-72.	0.6	59
9	Electrical and structural characterization of ultrathin epitaxial CoSi <sub>2</sub> on Si(111). Applied Physics Letters, 1987, 51, 1895-1897.	3.3	51
10	Origin of A- or B-type NiSi <sub>2</sub> determined by in situ transmission electron microscopy and diffraction during growth. Physical Review Letters, 1988, 60, 1158-1161.	7.8	50
11	Nonequilibrium segregation and trapping phenomena during ion-induced crystallization of amorphous Si. Physical Review Letters, 1988, 60, 1322-1325.	7.8	49
12	Control of epitaxial orientation of Si on CoSi <sub>2</sub> (111). Applied Physics Letters, 1988, 52, 1611-1613.	3.3	48
13	In-situ transmission electron microscopy of NiSi <sub>2</sub> formation by molecular beam epitaxy. Surface Science, 1989, 208, 317-350.	1.9	47
14	Subboundary-free zone melt recrystallization of thin film silicon. Applied Physics Letters, 1987, 51, 1256-1258.	3.3	42
15	Radiation-enhanced diffusion of Au in amorphous Si. Applied Physics Letters, 1988, 52, 1213-1215.	3.3	38
16	Stability of visible luminescence from porous silicon. Applied Physics Letters, 1993, 62, 2667-2669.	3.3	36
17	Coreless defects and the continuity of epitaxial NiSi <sub>2</sub> /Si(100) thin films. Applied Physics Letters, 1988, 52, 828-830.	3.3	32
18	Growth of Thin Epitaxial CoSi <sub>2</sub> Layers on Si(100). Materials Research Society Symposia Proceedings, 1988, 116, 439.	0.1	25

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19	Twin formation and Au segregation during ion-beam-induced epitaxy of amorphous Si. Applied Physics Letters, 1988, 52, 1043-1045.	3.3	22
20	Si <sub>1-x</sub> CoSi <sub>2</sub> Structures: Pseudomorphism, Interface Structures, Epitaxial Orientations, and the Control of Pinholes. Journal of the Electrochemical Society, 1989, 136, 815-819.	2.9	22
21	High-resolution electron microscopy of interfaces and surfaces. Ultramicroscopy, 1987, 22, 35-46.	1.9	17
22	Microscopic Processes in Crystallisation. Solid State Phenomena, 1994, 37-38, 257-268.	0.3	17
23	Trapping of Au in Si during pulsed laser irradiation: A comparison with ion beam induced segregation. Applied Physics Letters, 1988, 53, 2486-2488.	3.3	16
24	Dependence of the structural and electrical properties of ultrathin cobalt silicide films on formation conditions. Journal of Materials Research, 1989, 4, 144-155.	2.6	16
25	Characterization of Ultrathin CoSi <sub>2</sub> on Si(111) Layers.. Materials Research Society Symposia Proceedings, 1987, 91, 445.	0.1	15
26	Rapid thermal processing to improve the epitaxy of (100)-silicon on (111,02) sapphire. Applied Physics Letters, 1987, 50, 466-468.	3.3	15
27	Epitaxial recrystallization and diffusion phenomena in amorphous silicon produced by MeV ion beams. Nuclear Instruments & Methods in Physics Research B, 1989, 37-38, 955-959.	1.4	12
28	Batstone and Phillips Reply. Physical Review Letters, 1988, 61, 2275-2275.	7.8	11
29	Twin intersections in silicon on sapphire. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1991, 63, 1037-1050.	0.6	11
30	Stacking fault asymmetry in epitaxial films of mcvd znse/gaas(001). Philosophical Magazine A: Physics of Condensed Matter, Structure, Defects and Mechanical Properties, 1992, 66, 609-620.	0.6	11
31	Ultrathin Single Crystal CoSi <sub>2</sub> Layers on Si(111) and Si(100). Materials Research Society Symposia Proceedings, 1987, 102, 265.	0.1	10
32	The Effect of Rapid Thermal Annealing on the Dislocation Structure of Silicon on Sapphire. Materials Research Society Symposia Proceedings, 1988, 138, 373.	0.1	10
33	Hot Electron Transistors Using Si/CoSi <sub>2</sub> . Materials Research Society Symposia Proceedings, 1987, 107, 259.	0.1	7
34	Radiation-enhanced diffusion of implanted impurities in amorphous Si. Nuclear Instruments & Methods in Physics Research B, 1989, 39, 343-346.	1.4	7
35	Hot Electron Transistors Using Si/CoSi <sub>2</sub> . Materials Research Society Symposia Proceedings, 1987, 102, 361.	0.1	6
36	Growth and characterization of ultrathin cobalt silicide films on Si(211) and (311). Journal of Materials Research, 1990, 5, 1032-1041.	2.6	6

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37	Techniques of Insulator/Semiconductor Heterostructure Specimen Preparation. Materials Research Society Symposia Proceedings, 1987, 115, 63.	0.1	5
38	The Role of Implant Temperature in the Formation of Thin Buried Oxide Layers. Materials Research Society Symposia Proceedings, 1986, 74, 585.	0.1	4
39	Electron Transport Through Epitaxial Metal/Semiconductor Heterostructures. Materials Research Society Symposia Proceedings, 1986, 77, 271.	0.1	4
40	The Effect of Rapid Thermal Annealing on Heteroepitaxial Structures. Materials Research Society Symposia Proceedings, 1991, 91, 365.	0.1	4
41	Microstructural Characterization of High Dose Oxygen Implanted Silicon. Materials Research Society Symposia Proceedings, 1986, 74, 597.	0.1	3
42	Correlation of Electrical Properties with Structure Imaging of Semiconductor Interfaces. Materials Research Society Symposia Proceedings, 1986, 82, 335.	0.1	3
43	Effect of Atomic Structure at the Epitaxial CaF <sub>2</sub> /Si(111) Interface on Electrical Properties. Materials Research Society Symposia Proceedings, 1987, 102, 45.	0.1	3
44	In-Situ Rapid Thermal Annealing of Heterostructures Grown by Molecular Beam Epitaxy. Materials Research Society Symposia Proceedings, 1987, 102, 355.	0.1	2
45	Electrical Transport in Ultrathin Films of CoSi <sub>2</sub> on Si(111). Materials Research Society Symposia Proceedings, 1987, 91, 427.	0.1	2
46	New Directions in the Growth of Epitaxial Insulators and Metals on Silicon. Materials Research Society Symposia Proceedings, 1988, 116, 403.	0.1	2
47	Reconstruction of (100) Silicon/Disilicide Interfaces. Materials Research Society Symposia Proceedings, 1989, 139, 97.	0.1	2
48	Dislocation Luminescence in ZnSe. Proceedings Annual Meeting Electron Microscopy Society of America, 1986, 44, 818-819.	0.0	2
49	Atomic structure imaging of the Si/SiO <sub>2</sub> interface with high-resolution electron microscopy. Proceedings Annual Meeting Electron Microscopy Society of America, 1986, 44, 390-391.	0.0	2
50	The Effect of Formation Conditions on the Structural and Electrical Properties of Ultrathin Cobalt Silicide Films. Materials Research Society Symposia Proceedings, 1987, 102, 389.	0.1	1
51	Segregation and Trapping of Gold During Ion-Induced Crystallization of Amorphous Si. Materials Research Society Symposia Proceedings, 1988, 100, 399.	0.1	1
52	Diffusion of Au in Amorphous Si During Ion-Beam Irradiation. Materials Research Society Symposia Proceedings, 1988, 100, 87.	0.1	1
53	Bonding Configurations at Epitaxial CaF <sub>2</sub> /Si Interfaces. Materials Research Society Symposia Proceedings, 1989, 139, 351.	0.1	1
54	High Resolution In Situ TEM Studies of Silicide-Mediated Crystallization of Amorphous Silicon. Materials Research Society Symposia Proceedings, 1993, 321, 579.	0.1	1

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55	Reconstruction of the NiSi <sub>2</sub> /Si(100) interface. Proceedings Annual Meeting Electron Microscopy Society of America, 1989, 47, 460-461.	0.0	1
56	Interface motion during recrystallization of amorphous NiSi <sub>2</sub> . Proceedings Annual Meeting Electron Microscopy Society of America, 1990, 48, 524-525.	0.0	1
57	Nucleation and Growth of Ultrathin Epitaxial Metal Silicides on Silicon. Materials Research Society Symposia Proceedings, 1987, 102, 253.	0.1	0
58	In-Situ Rapid Thermal Annealing of Heterostructures Grown by Molecular Beam Epitaxy. Materials Research Society Symposia Proceedings, 1987, 107, 253.	0.1	0
59	In-Situ Studies of the MBE Growth of CoSi <sub>2</sub> on Si (111) in a UHV Transmission Electron Microscope. Materials Research Society Symposia Proceedings, 1987, 94, 151.	0.1	0
60	Motion of Crystal/Crystal and Crystal/Amorphous Interfaces. Materials Research Society Symposia Proceedings, 1990, 183, 79.	0.1	0
61	Kinetic Studies of Nanoscale Crystallization in Electronic Materials. Materials Research Society Symposia Proceedings, 1995, 405, 73.	0.1	0
62	Opportunities and Challenges of Global Network Cameras. , 2015, , .		0
63	TEM and cathodoluminescence of precipitates in II-VI semiconductors. Proceedings Annual Meeting Electron Microscopy Society of America, 1988, 46, 488-489.	0.0	0
64	A crystallographic analysis of the CoSi/Si(111) interface using Transmission Electron Microscopy. Proceedings Annual Meeting Electron Microscopy Society of America, 1990, 48, 574-575.	0.0	0
65	Degradation of visible cathodoluminescence from porous silicon. Proceedings Annual Meeting Electron Microscopy Society of America, 1992, 50, 1372-1373.	0.0	0
66	In situ crystallization of amorphous silicon. Proceedings Annual Meeting Electron Microscopy Society of America, 1992, 50, 1346-1347.	0.0	0
67	Dynamic studies of silicide-mediated crystallization of amorphous silicon. Proceedings Annual Meeting Electron Microscopy Society of America, 1992, 50, 1352-1353.	0.0	0
68	Structural and electronic properties of defects in semiconductors. Proceedings Annual Meeting Electron Microscopy Society of America, 1995, 53, 4-5.	0.0	0
69	Epitaxial films of CoSi <sub>2</sub> on Si (311) and Si (211). Proceedings Annual Meeting Electron Microscopy Society of America, 1989, 47, 456-457.	0.0	0